

Ultra High Sensitivity Hall Effect Latch

1. Description

iA1188D Hall-effect sensor is a temperature stable, stress-resistant sensor. Superior high-temperature performance is made possible through a dynamic offset cancellation that utilizes chopper-stabilization. This method reduces the offset voltage normally caused by device over molding, temperature dependencies, and thermal stress.

iA1188D includes the following on a single silicon chip: voltage regulator, Hall voltage generator, small-signal amplifier, chopper stabilization, Schmitt trigger. Advanced DMOS wafer fabrication processing is used to take advantage of low-voltage requirements, component matching, very low input-offset errors, and small component geometries.

This device requires the presence of both south and north polarity magnetic fields for operation. In the presence of a south polarity field of sufficient strength, the device output sensor on, and only switches off when a north polarity field of sufficient strength is present.

iA1188D is rated for operation between the ambient temperatures -40°C to 125°C . The two package styles available provide magnetically optimized solutions for most applications. iA1188D is an SOT-23, a miniature low-profile surface-mount package.

Package is Halogen Free standard and which have been verified by third party lab.

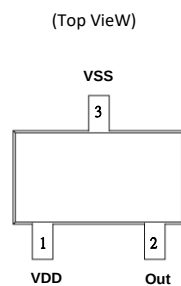
2. Features

- DMOS Hall IC Technology.
- Reverse bias protection on power supply pin.
- Chopper stabilized amplifier stage.
- Optimized for BLDC motor applications.
- Reliable and low shifting on high Temp condition.
- Good ESD Protection.

3. Applications

- High temperature Fan motor
- 3 phase BLDC motor application
- Speed sensing
- Position sensing
- Current sensing
- Revolution counting
- Solid-State Switch
- Linear Position Detection
- Angular Position Detection
- Proximity Detection
- High ESD Capability

4. Pin Assignments

**SOT-23**

5. Marking Information

Product Name	Package	Marking
iA1188D	SOT-23	188XX X: Date Code

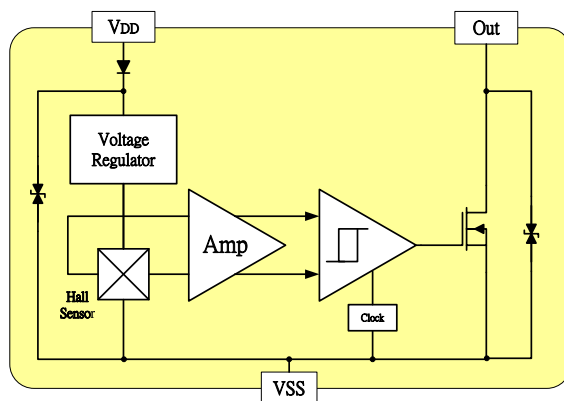
6. Ordering Code

iA1188D

7. Pin Definitions

Name	Pin	Description
V _{DD}	1	Power Supply
V _{OUT}	2	Output
V _{SS}	3	Ground

8. Block Diagram



9. Absolute Maximum Ratings

($T_A = 25\text{ }^{\circ}\text{C}$)

Characteristics		Values	Unit
Supply Voltage (V_{DD})		28	V
Output Voltage (V_{out})		28	V
Reverse Voltage (V_{DD} / V_{out})		-28/-0.3	V
Output current (I_{SINK})		50	mA
Operating Temperature Range (T_A)		-40 ~ +125	$^{\circ}\text{C}$
Storage temperature Range (T_s)		-65 ~ +150	$^{\circ}\text{C}$
Maximum Junction Temp (T_J)		150	$^{\circ}\text{C}$
Thermal Resistance	(θ_{JA})	543	$^{\circ}\text{C}/\text{w}$
	(θ_{JC})	410	$^{\circ}\text{C}/\text{w}$
Package Power Dissipation (P_D)		230	mW

iA1188D

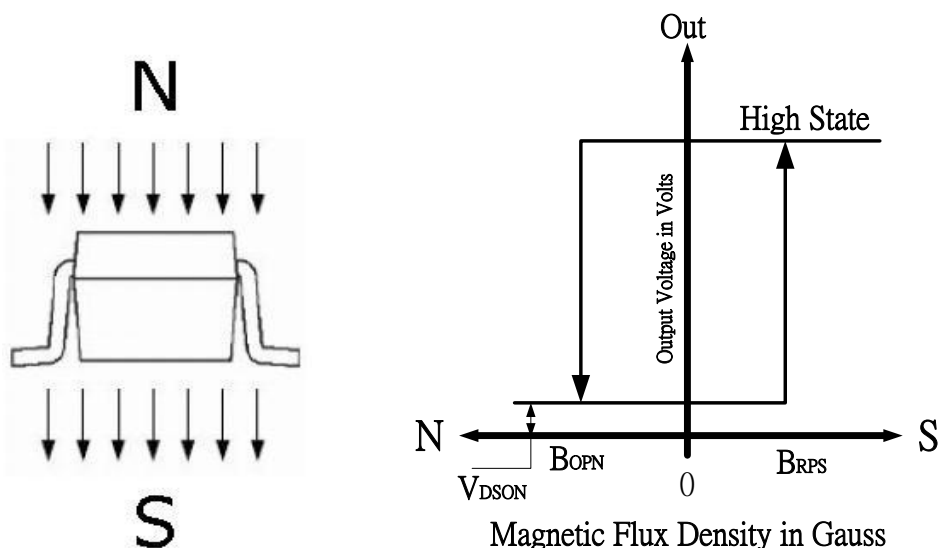
10. Electrical Characteristics

(DC Operating Parameters : $T_A = +25^\circ\text{C}$, $V_{DD} = 12\text{V}$)

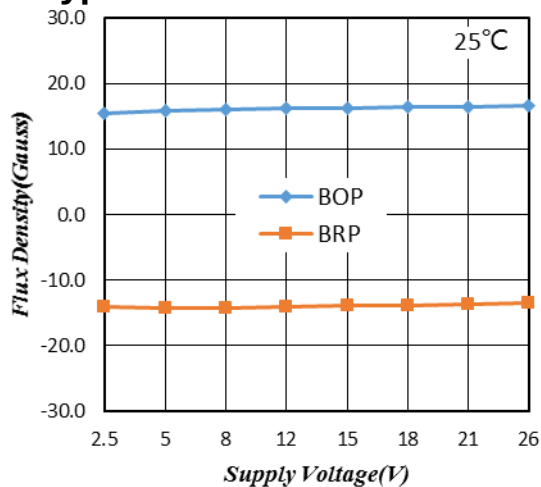
Parameters	Test Conditions	Min	Typ	Max	Units
Supply Voltage (V_{DD})	Operating	2.5		26.0	V
Supply Current (I_{DD})	$B < B_{OP}$			5.0	mA
Output Saturation Voltage, (V_{DSON})	$I_{out} = 20\text{mA}$, $B > B_{OP}$			400.0	mV
Output Leakage Current, (I_{off})	I_{OFF} $B < B_{RP}$, $V_{OUT} = 12\text{V}$			10.0	μA
Output Rise Time, (T_R)	$R_L = 1.1\text{K}\Omega$, $C_L = 20\text{pF}$		0.04	0.45	μS
Output Fall Time, (T_F)	$R_L = 820\Omega$; $C_L = 20\text{pF}$		0.18	0.45	μS
Electro-Static Discharge	HBM	4			KV
Operate Point, (B_{OP})		-25		-5	Gauss
Release Point, (B_{RP})		5		25	Gauss
Hysteresis (B_{HYS})	$ B_{OP} - B_{RP} $		30		Gauss

11. Output Behavior versus Magnetic Polar

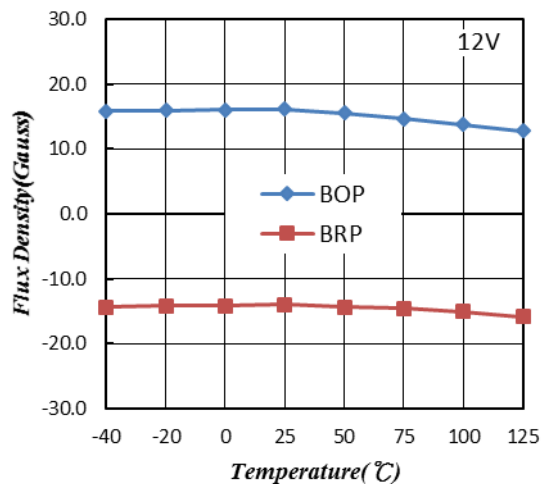
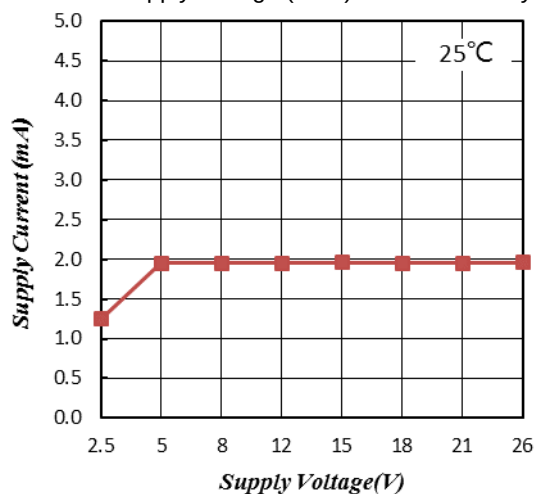
(DC Operating Parameters $T_A = -40$ to 125°C , $V_{DD} = 2.5$ to 24V)



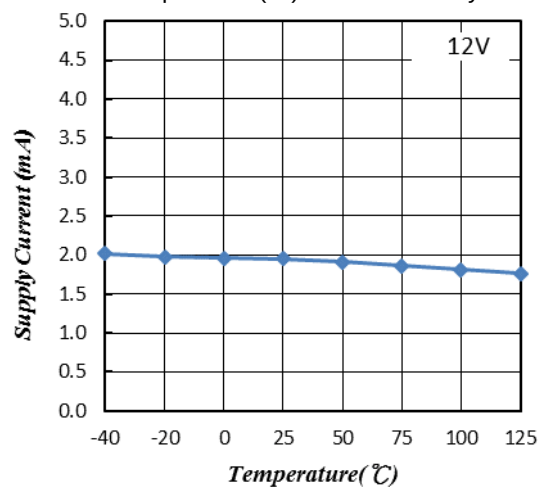
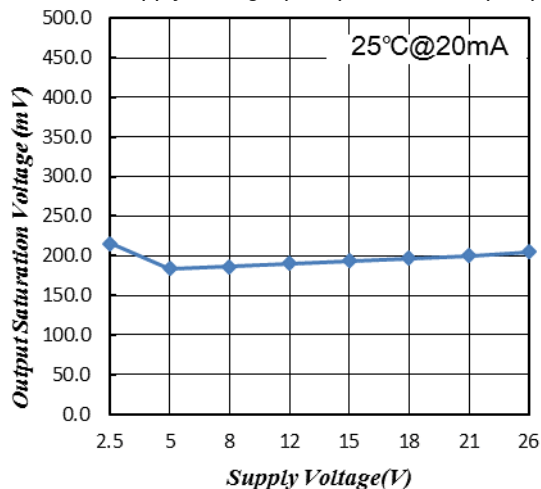
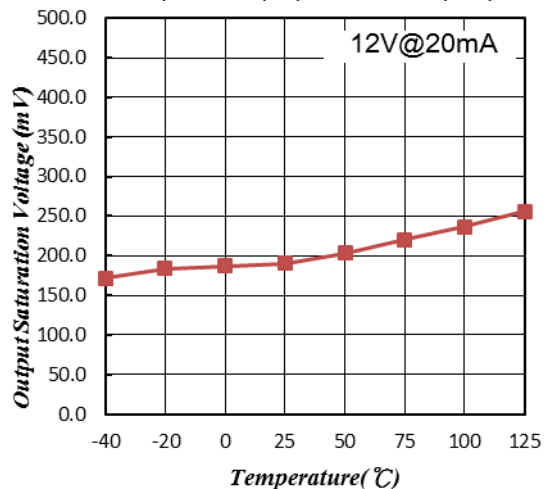
12. Typical Characteristics



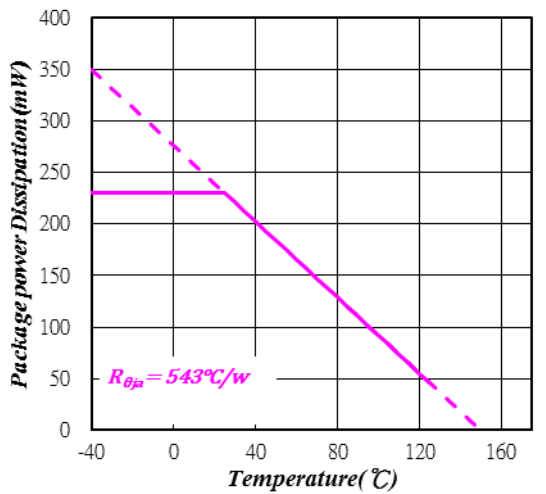
Supply Voltage (VDD) Vs. Flux Density

Temperature (T_A) Vs. Flux Density

Supply Voltage (VDD) Vs. Current (IDD)

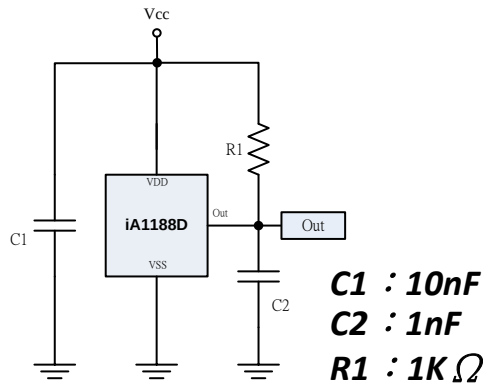
Temperature (T_A) Vs. Current (IDD)Supply Voltage (V_{DD}) Vs. Output Voltage (V_{DSON})Temperature (T_A) Vs. Output Voltage (V_{DSON})

12. Typical Characteristics (Cont.)



Power Dissipation Vs. Temperature (T_A)

13. Typical Application circuit

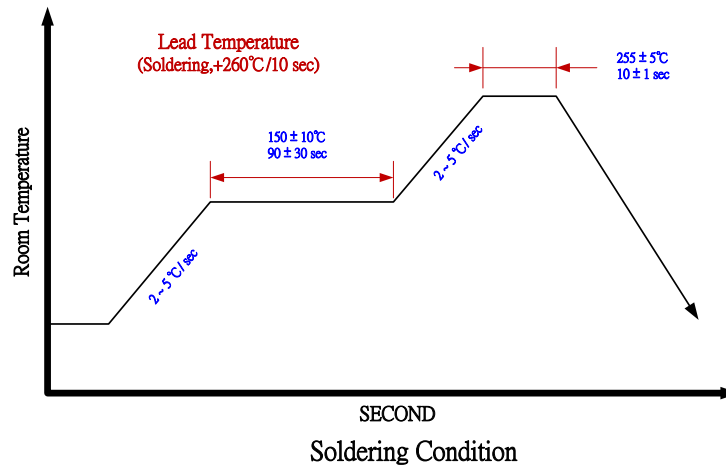


14. Package Power Dissipation

The power dissipation of the Package is a function of the pad size. This can vary from the minimum pad size for soldering to a pad size given for maximum power dissipation. Power dissipation for a surface mount device is determined by $T_{J(max)}$, the maximum rated junction temperature of the die, $R_{\theta JA}$, the thermal resistance from the device junction to ambient, and the operating temperature, T_a . Using the values provided on the data sheet for the package, PD can be calculated as follows:

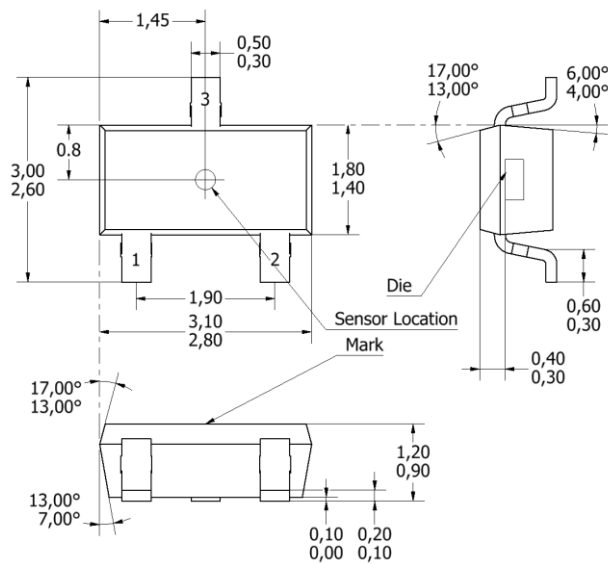
$$P_D = \frac{T_{J(max)} - T_a}{R_{\theta ja}}$$

15. IR reflow curve



16. Package Dimensions

SOT-23 Package (Top View)



NOTES:

1. Controlling dimension: mm
2. Leads must be free of flash and plating voids
3. Lead thickness after solder plating will be 0.254mm maximum
4. (For reference only) Land Pattern

